

Schottky barrier diode

RB520G-30

●Applications

Rectifying small power.

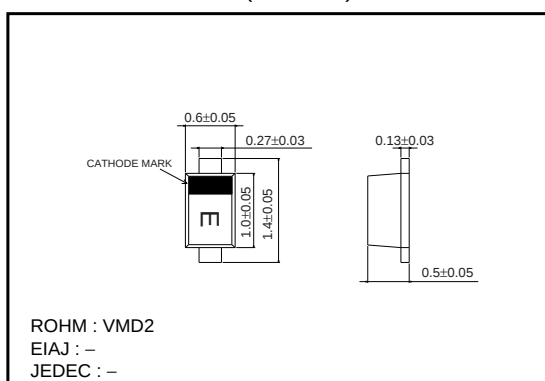
●Features

- 1) Ultra small mold type. (VMD2)
- 2) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	100	mA
Forward peak surge current (60Hz•1cyc.)	I_{FSM}	500	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40 to +125	°C

* 60Hz, 1 ϕ

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	0.45	V	$I_F=10\text{mA}$
Reverse current	I_R	—	—	0.5	μA	$V_R=10\text{V}$

* Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

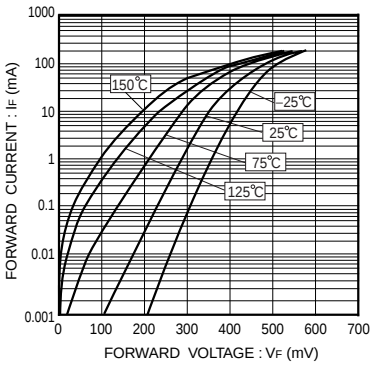


Fig.1 Forward characteristics

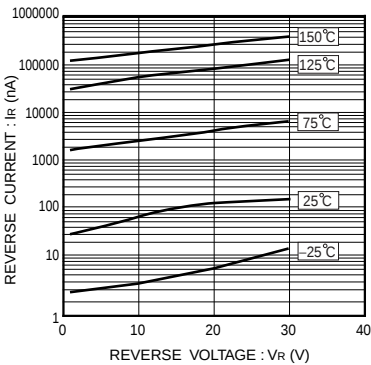


Fig.2 Reverse characteristics

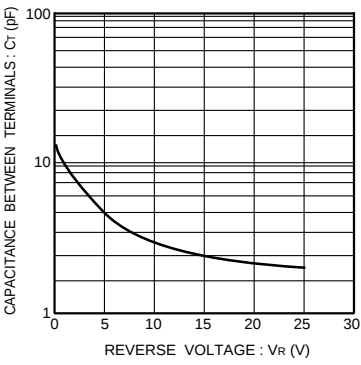


Fig. 3 Capacitance between terminals characteristics